



**T\ Yfa U fYg]ghLbW\**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub>	-	-	1.8	° C/W
Thermal resistance, junction - ambient	R <sub>thJA</sub>	-	-	45	° C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>	-	-	265	° C

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60			V
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.6	2.5	V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1.0	uA
Gate- Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			100	nA
Static Drain-source On Resistance	□	V <sub>GS</sub> =10V, I <sub>D</sub> =24A				
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =12A				
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =25V, I <sub>D</sub> =10A				
Source-drain voltage	V <sub>SD</sub>	I <sub>S</sub> =24A				

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C <sub>iss</sub>	f = 1MHz	-	3220	-	pF
Output capacitance	C <sub>oss</sub>		-	149	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	106	-	

**Gate Charge characteristics(Ta= 25 )**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> =25V	-	30	-	nC
Gate - Source charge	Q <sub>gs</sub>	I <sub>D</sub> = 8A	-	9	-	
Gate - Drain charge	Q <sub>gd</sub>	V <sub>GS</sub> = 10V	-	15	-	

Note:

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Dimensions(TO-252)

Unit mm

SYMBOL	mi n	max	SYMBOL	mi n	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

